

ENGLISH

JAPANESE

HELP

REPORT

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Notes:

1. Untranslatable words are replaced with asterisks (*****).
2. Texts in the figures are not translated and shown as it is.

Translated: 22:51:19 JST 11/13/2007

Dictionary: Last updated 10/12/2007 / Priority:

[Document Name] Abstract

[Abstract]

[A technical problem] The reduction in cost and highly-efficient-izing of photoelectrical conversion equipment containing the crystalline material silicon system thin film photoelectrical conversion layer formed using the low-temperature process by a plasma CVD method are attained.

[Means for Solution] Silicon system thin film photoelectrical conversion equipment contains the back electrode 10 and at least one silicon system photoelectrical conversion unit 11 which have a substrate 1 and the light reflex nature metal membrane 102, and the front transparent electrode 2. Either [at least] the light reflex nature metal membrane 102 or the front transparent electrode 2 has surface unevenness form in the field by the side of a silicon system photoelectrical conversion unit, and while a concavo-convex vertical interval is in within the limits which is 0.01-2 micrometers, a concavo-convex pitch is within the limits of the 25 or less times more greatly than a vertical interval.

[A selection figure] drawing 1

[Translation done.]